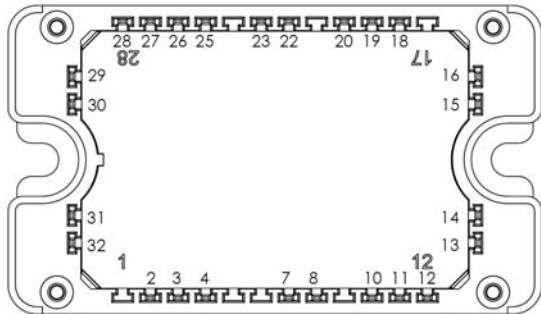
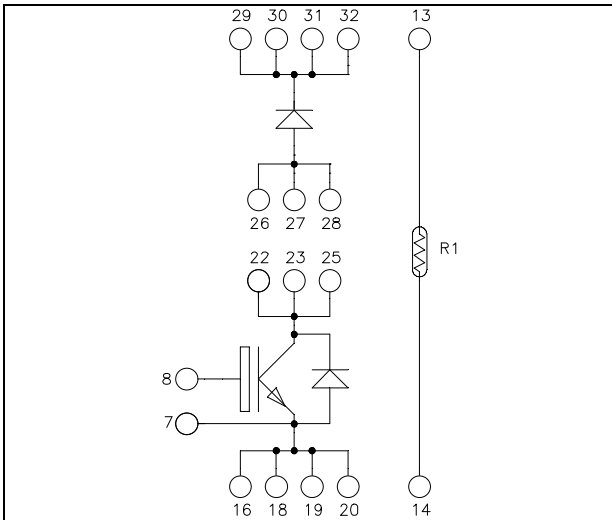


**Boost chopper  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 200A @ T_c = 100^\circ C$**



Pins 29/30/31/32 must be shorted together

Pins 26/27/28/22/23/25 must be shorted together to achieve a phase leg

Pins 16/18/19/20 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

### Features

- **Trench + Field Stop IGBT3**
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

### Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

**All ratings @  $T_j = 25^\circ C$  unless otherwise specified**

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Voltage	600	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	290
		$T_c = 100^\circ C$	200
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	400
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Power Dissipation	$T_c = 25^\circ C$	750
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	400A @ 550V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I <sub>CES</sub>	Zero Gate Voltage Collector Current	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V			250	μA
V <sub>CE(sat)</sub>	Collector Emitter Saturation Voltage	V <sub>GE</sub> = 15V I <sub>C</sub> = 200A		T <sub>j</sub> = 25°C 1.5 T <sub>j</sub> = 150°C 1.7	1.9	V
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 2 mA	5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	V <sub>GE</sub> = 20V, V <sub>CE</sub> = 0V			400	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C <sub>ies</sub>	Input Capacitance	V <sub>GE</sub> = 0V		12.3		nF
C <sub>oes</sub>	Output Capacitance	V <sub>CE</sub> = 25V		0.8		
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		0.4		
Q <sub>G</sub>	Gate charge	V <sub>GE</sub> = ±15V ; V <sub>CE</sub> = 300V I <sub>C</sub> = 200A		2.2		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C) V <sub>GE</sub> = ±15V V <sub>Bus</sub> = 300V I <sub>C</sub> = 200A R <sub>G</sub> = 2Ω		115		ns
T <sub>r</sub>	Rise Time			45		
T <sub>d(off)</sub>	Turn-off Delay Time			225		
T <sub>f</sub>	Fall Time			55		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) V <sub>GE</sub> = ±15V V <sub>Bus</sub> = 300V I <sub>C</sub> = 200A R <sub>G</sub> = 2Ω		130		ns
T <sub>r</sub>	Rise Time			50		
T <sub>d(off)</sub>	Turn-off Delay Time			300		
T <sub>f</sub>	Fall Time			70		
E <sub>on</sub>	Turn on Energy	V <sub>GE</sub> = ±15V V <sub>Bus</sub> = 300V		T <sub>j</sub> = 25°C 1 T <sub>j</sub> = 150°C 1.8		mJ
E <sub>off</sub>	Turn off Energy	I <sub>C</sub> = 200A R <sub>G</sub> = 2Ω		T <sub>j</sub> = 25°C 5.7 T <sub>j</sub> = 150°C 7		mJ
I <sub>sc</sub>	Short Circuit data	V <sub>GE</sub> ≤ 15V ; V <sub>Bus</sub> = 360V t <sub>p</sub> ≤ 6μs ; T <sub>j</sub> = 150°C		1000		A
R <sub>thJC</sub>	Junction to Case Thermal Resistance				0.20	°C/W

## Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage				600	V
I <sub>RM</sub>	Reverse Leakage Current	V <sub>R</sub> = 600V			250	μA
I <sub>F</sub>	DC Forward Current			T <sub>c</sub> = 80°C 200		A
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 200A V <sub>GE</sub> = 0V		T <sub>j</sub> = 25°C 1.6 T <sub>j</sub> = 150°C 1.5	2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 200A V <sub>R</sub> = 300V di/dt = 2800A/μs		T <sub>j</sub> = 25°C 125 T <sub>j</sub> = 150°C 220		ns
Q <sub>rr</sub>	Reverse Recovery Charge			T <sub>j</sub> = 25°C 9 T <sub>j</sub> = 150°C 20		μC
Er	Reverse Recovery Energy			T <sub>j</sub> = 25°C 2.2 T <sub>j</sub> = 150°C 4.8		mJ
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.31

## Thermal and package characteristics

Symbol	Characteristic	Min	Max	Unit		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V		
T <sub>J</sub>	Operating junction temperature range	-40	175	°C		
T <sub>JOP</sub>	Recommended junction temperature under switching conditions	-40	T <sub>Jmax</sub> -25			
T <sub>STG</sub>	Storage Temperature Range	-40	125			
T <sub>C</sub>	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

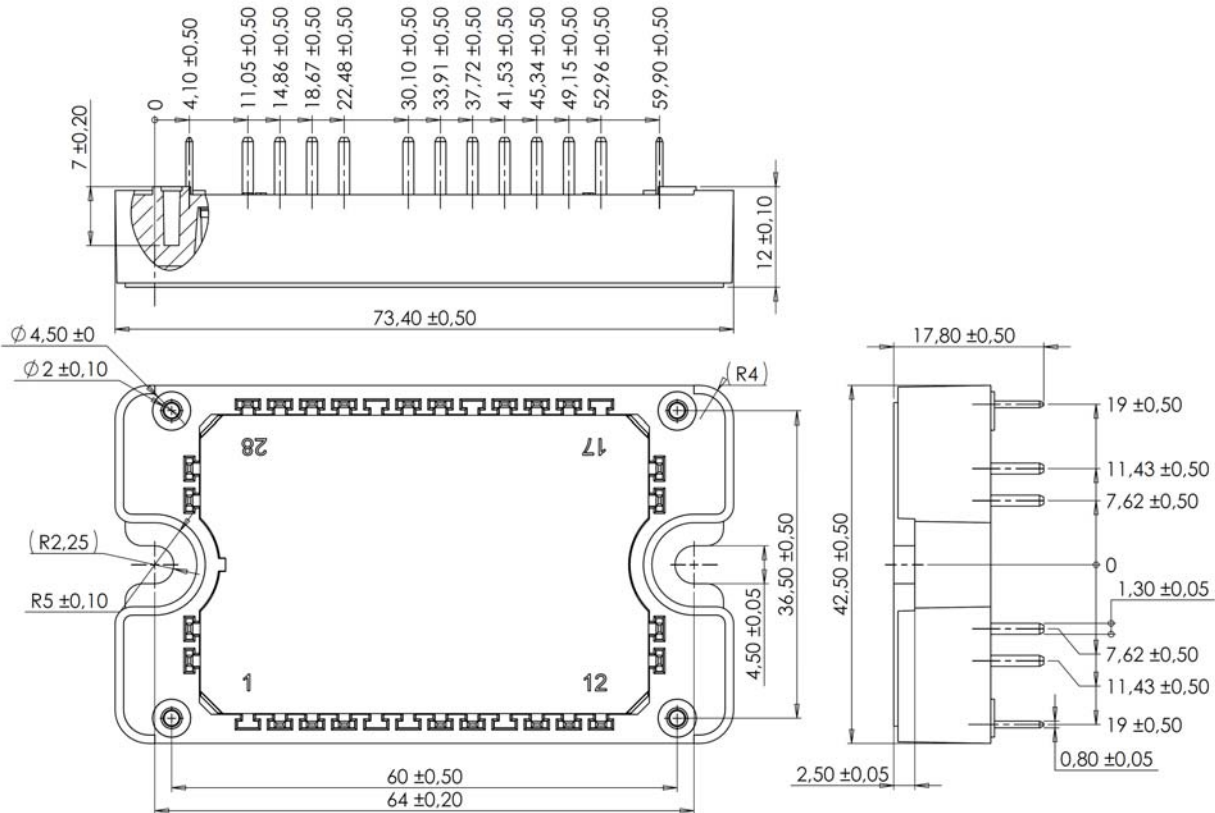
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
ΔR <sub>25</sub> /R <sub>25</sub>			5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K
ΔB/B	T <sub>C</sub> = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

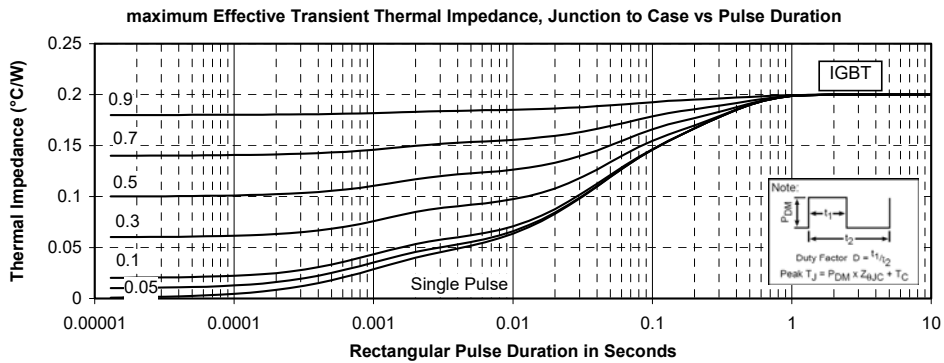
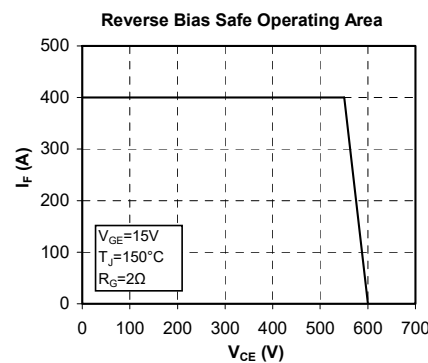
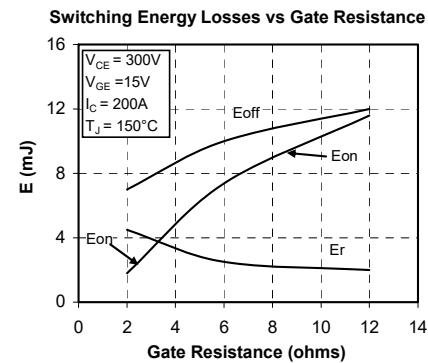
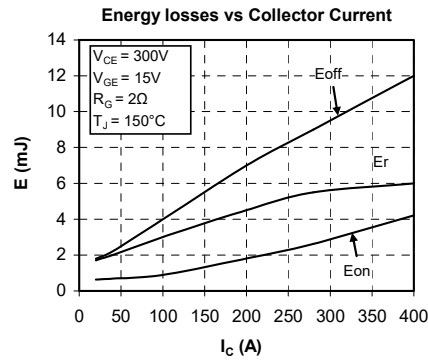
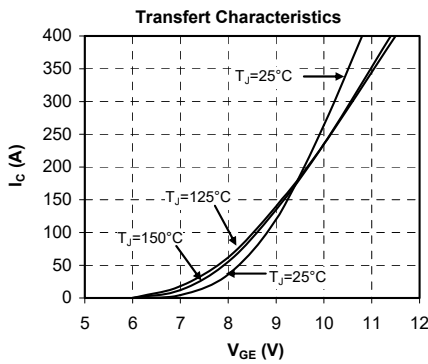
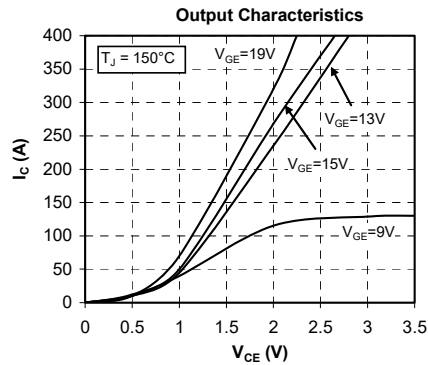
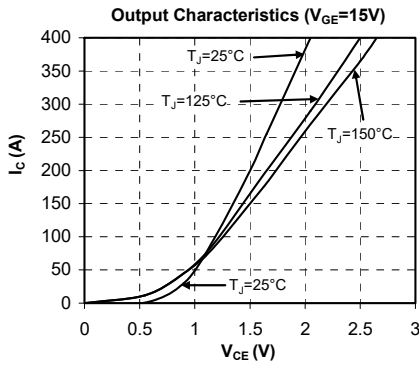
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

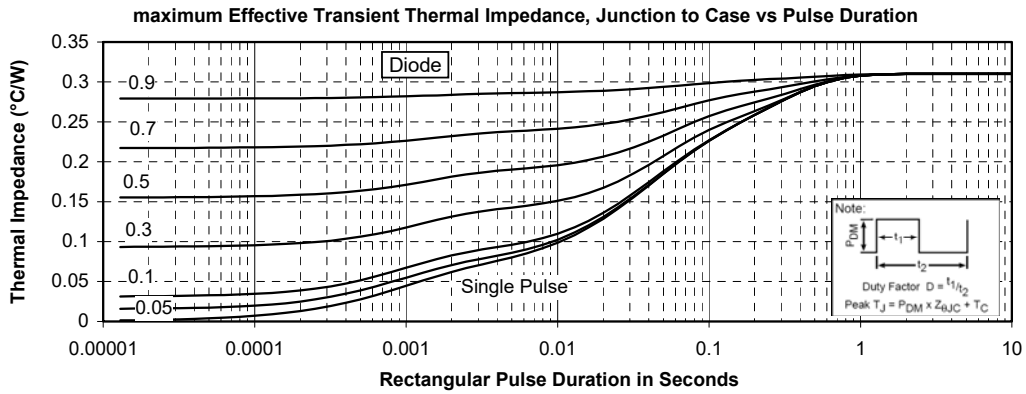
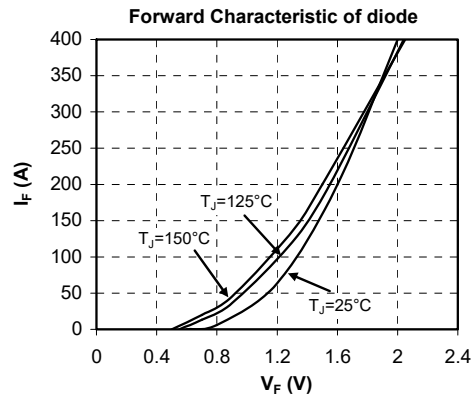
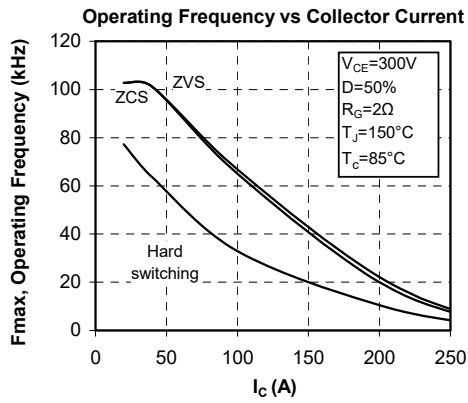
## Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





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